
HZS-LL Series

Silicon Epitaxial Planar Zener Diode for Hard Knee Low Noise

HITACHI

ADE-208-122A(Z)

Rev 1

Dec. 1996

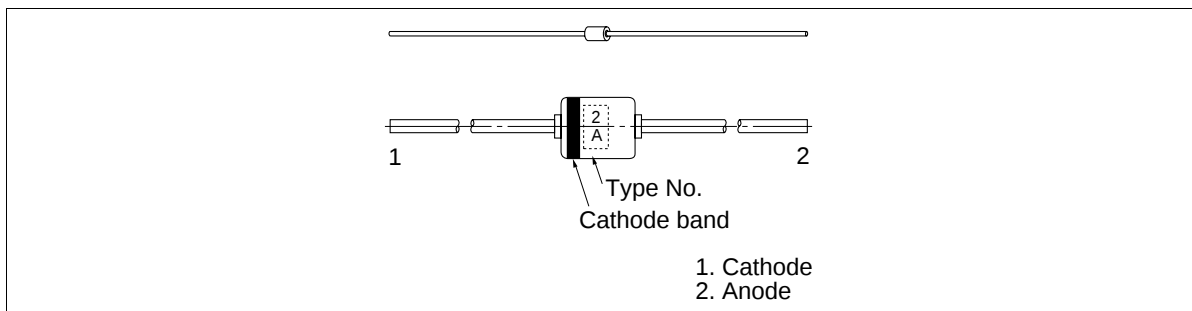
Features

- V_Z - I_Z characteristics are semilogarithmic linear from $I_Z=1\text{nA}$ to 1mA and have sharper breakdown knees in a low current region, and also lower V_Z temperature coefficients .
- Low dynamic impedance and low noise in the low current region (approximately 1/10 lower than the current zeners).
- Suitable for 5mm-pitch high speed automatic insertion.

Ordering Information

Type No.	Mark	Package Code
HZS-LL Series	Type No.	MHD

Outline



HZS-LL Series

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	Pd	250	mW
Junction temperature	Tj	175	°C
Storage temperature	Tstg	-55 to +175	°C

Electrical Characteristics (Ta = 25°C)

		VZ(V) *1		IR(nA)		ZZT(Ω)		ZZK(kΩ)*2		ΔVZ1(V) *3	ΔVZ2(V) *3	
Type	Grade	Min	Max	IZ(mA)	Max	VR(V)	Max	IZT(mA)	Typ	IZK(μA)	Max	Max
HZS2LL	A	1.6	2.0	0.5	100	0.5	350	0.5	(1.2)	50	0.5	0.6
	B	1.9	2.3									
	C	2.2	2.6									
HZS3LL	A	2.5	2.9	0.5	100	1.0	360	0.5	(1.2)	50	0.5	0.6
	B	2.8	3.2									
	C	3.1	3.5									
HZS4LL	A	3.4	3.8	0.5	100	2.0	370	0.5	(1.5)	50	0.5	0.6
	B	3.7	4.1									
	C	4.0	4.4									
HZS5LL	A	4.3	4.7	0.5	100	3.0	380	0.5	(1.5)	50	0.5	0.6
	B	4.6	5.0									
	C	4.9	5.3									

Note: 1. Tested with DC.

Note: 2. Reference only.

Note: 3. $\Delta VZ1 = VZ (IZ = 0.5 \text{ mA}) - VZ1 (IZ = 0.05 \text{ mA})$ $\Delta VZ2 = VZ1 (IZ = 0.05 \text{ mA}) - VZ2 (IZ = 0.001 \text{ mA})$

Note: 4. Type No. is as follows; HZS2ALL, HZS2BLL, HZS5CLL.

Main Characteristic

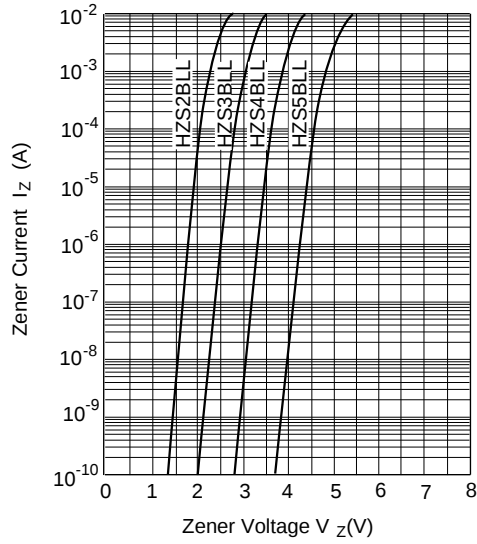


Fig.1 Zener current Vs. Zener voltage

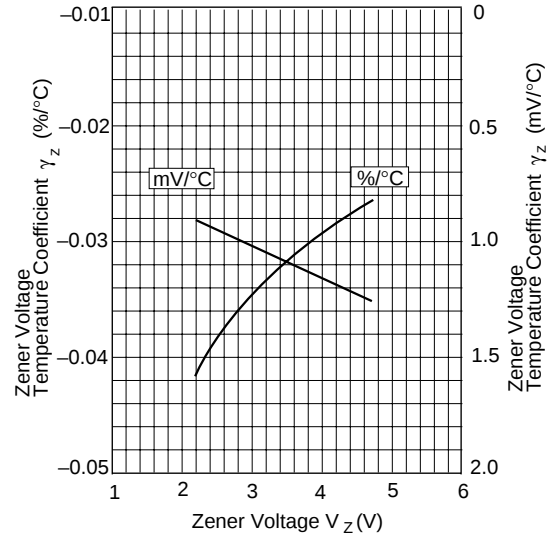


Fig.2 Temperature Coefficient Vs. Zener voltage

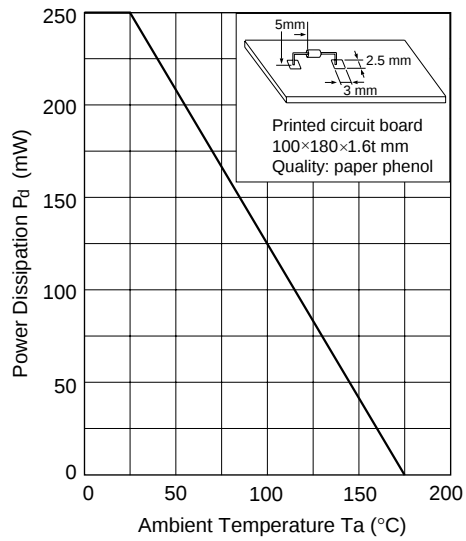


Fig.3 Power Dissipation Vs. Ambient Temperature

HZS-LL Series

Package Dimensions

Unit : mm

